DOCKET

2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cabral, Jr. et al.

Serial No.: 09/902,483 Group Art Unit: 2813

Filing Date: July 11, 2001 Examiner: Erik Kielin

For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY CONTACTS TO THIN FILM SILICIDE-ON-INSULATOR AND BULK MOSFETS AND FOR SHALLOW JUNCTIONS

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

EXCESS CLAIM FEE PAYMENT LETTER

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	AFTER AMENDMENT	PREV. PAID FOR	EXTRA CLAIMS PRESENT	RATE	FEE DUE
Total Claims	16 -	22	= 0	x $18.00	$ 0.00
Indep. Claims	6 -	4	= 2	x $84.00	$ 168.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					**$ 168.00**

Please charge Assignee's Deposit Account No. 50-0510 the amount of $168.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed.

The Commissioner is authorized charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 50-0510.

Respectfully Submitted,

Date: May 14, 2002

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Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated February 14, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please replace the paragraph on page 11, line 6 with the following paragraph:

A1 Figures 9A and 9B illustrate the novelty of the inventive structure.

Please replace the paragraph on page 12, line 6 with the following paragraph:

A2 Referring to Figure 2, a metal 20 (e.g., Co, Ni, Ti, Pd, Pt or alloys thereof) is deposited in a thickness within a range of about 7-8 nm. A TiN cap or a W cap 21 is deposited over the metal 20 to prevent oxidation during the anneal. The metal 20 is reacted with silicon in the source 4, drain 5, and gate 7 regions at a low temperature T_1. It is noted that if the temperature is too low,